

TOSHIBA VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR TYPE

JDV4P08U

VCO FOR UHF BAND RADIO

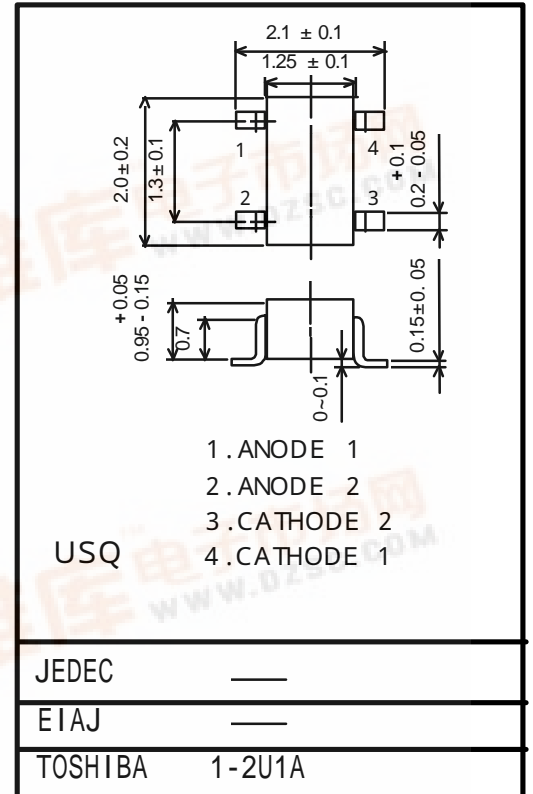
Small Package

Ultra Low Series Resistance : $r_s = 0.30$ (Typ.)

MAXIMUM RATINGS($T_a = 25$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	VR	10	V
Junction Temperature	Tj	125	
Storage Temperature Range	Tstg	- 55 ~ 125	

Unit in mm



ELECTRICAL CHARACTERISTICS ($T_a=25$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	VR	$I_R = 1 \mu A$	10	-	-	V
Reverse Current	IR	$V_R = 10 V$	-	-	3	nA
Capacitance	C1V	$V_R = 1 V$, $f = 1 MHz$	17.3	18.3	19.3	pF
Capacitance	C4V	$V_R = 4 V$, $f = 1 MHz$	5.3	6.1	6.6	pF
Capacitance Ratio	C1V / C4V	-	2.8	3.0	-	-
Series Resistance	r_s	$V_R = 1 V$, $f = 470 MHz$	-	0.3	0.5	

Marking

